

Abstract

In performing an anisotropic etching process after a taper etching process of a gate conductive layer of a two-layer or three-layer laminated structure, a portion that is not etched is left at an edge of a second conductive film to shorten an LDD region. It is an object to make the LDD region longer by reducing or removing the left portion that is not etched. After a taper etching process of a gate conductive layer of a two-layer or three-layer laminated structure, an argon plasma treatment is performed. With this argon plasma treatment, a reaction product in the taper etching process is removed, and it becomes possible to reduce or remove the left portion that is not etched in the anisotropic etching to be performed next.